# **DISCRETE SEMICONDUCTORS**

# DATA SHEET

**PEMB11; PUMB11** PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

Product data sheet Supersedes data of 2001 Sep 13

2003 Oct 03



# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

PEMB11; PUMB11

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

# **APPLICATIONS**

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
TR1	PNP	_	_	_
TR2	PNP	-	-	-

10

10

 $k\Omega$ 

 $k\Omega$ 

**QUICK REFERENCE DATA** 

bias resistor

bias resistor

# **DESCRIPTION**

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

# **PRODUCT OVERVIEW**

TYPE NUMBER	PAC	(AGE	MARKING CODE(1)	NPN/PNP	NPN/NPN	
TIPE NOMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT	
PEMB11	SOT666	_	B1	PEMD3	PEMH11	
PUMB11	SOT363	SC-88	B*1	PUMD3	PUMH11	

R1

R2

# Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

# SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
ITPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION	
PEMB11	6 5 4	1	emitter TR1	
PUMB11	6 5 4	2	base TR1	
	R1 R2	3	collector TR2	
	TR2	4	emitter TR2	
	TR1	5	base TR2	
		6	collector TR1	
	Top view MAM477			
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# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

PEMB11; PUMB11

# **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE					
ITPE NUMBER	NAME	DESCRIPTION	VERSION				
PEMB11	_	plastic surface mounted package; 6 leads	SOT666				
PUMB11	_	plastic surface mounted package; 6 leads	SOT363				

# **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transi	stor	,	<b>'</b>	<b>-</b>	-
$V_{CBO}$	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-10	V
VI	input voltage				
	positive		_	+10	V
	negative		_	-40	V
I <sub>O</sub>	output current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device	•				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	300	mW
	SOT666	notes 1 and 2	_	300	mW

# **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	-	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-400	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	30	_	_	
V <sub>CEsat</sub>	saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-1.1	-0.8	V
$V_{i(on)}$	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -10 \text{ mA}$	-2.5	-1.8	_	V
R1	input resistor		7	10	13	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	3	pF

# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

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**EUROPEAN** 

**PROJECTION** 

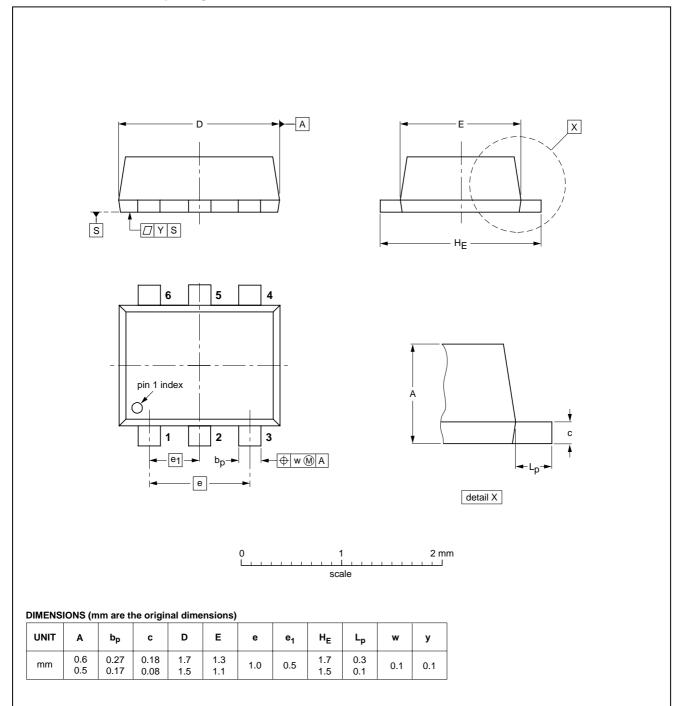
**ISSUE DATE** 

<del>-01-01-04</del> 01-08-27

# **PACKAGE OUTLINES**

Plastic surface mounted package; 6 leads

SOT666



**REFERENCES** 

EIAJ

**JEDEC** 

IEC

OUTLINE VERSION

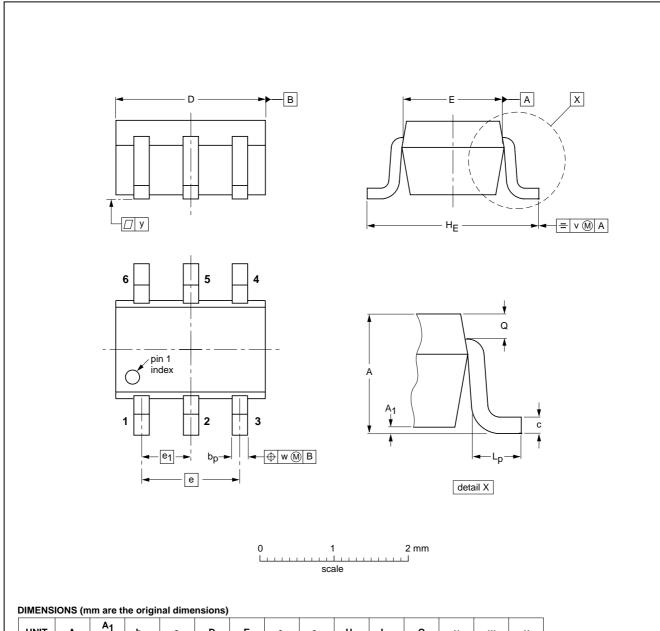
SOT666

# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

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# Plastic surface mounted package; 6 leads

**SOT363** 



UNIT	A	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	ø	V	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	EUROPEAN ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# **Contact information**

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